

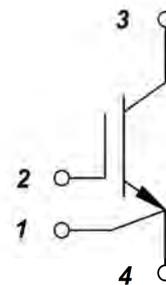
PRODUCT FEATURES

- High short circuit capability, self limiting short circuit current
- IGBT CHIP(T4 Fast Trench+Field Stop technology)
- $V_{CE(sat)}$ with positive temperature coefficient
- Fast switching and short tail current
- Popular SOT-227 Package



APPLICATIONS

- High frequency switching application
- Medical applications
- Motion/servo control
- UPS systems



IGBT

ABSOLUTE MAXIMUM RATINGS

$T_C=25^{\circ}\text{C}$ unless otherwise specified

Symbol	Parameter/Test Conditions		Values	Unit
V_{CES}	Collector Emitter Voltage	$T_J=25^{\circ}\text{C}$	1200	V
V_{GES}	Gate Emitter Voltage		± 20	
I_C	DC Collector Current	$T_C=25^{\circ}\text{C}$	150	A
		$T_C=95^{\circ}\text{C}$	100	
I_{CM}	Repetitive Peak Collector Current	$t_p=1\text{ms}$	200	
P_{tot}	Power Dissipation Per IGBT		550	W

MODULE CHARACTERISTICS

$T_C=25^{\circ}\text{C}$ unless otherwise specified

Symbol	Parameter/Test Conditions		Values	Unit
T_{Jmax}	Max. Junction Temperature		175	$^{\circ}\text{C}$
T_{Jop}	Operating Temperature		-40~150	
T_{stg}	Storage Temperature		-40~125	
V_{isol}	Isolation Breakdown Voltage	AC, 50Hz(R.M.S), $t=1\text{minute}$	3000	V
Torque	to heatsink	Recommended (M4)	0.7~1.1	Nm
	to terminal	Recommended (M4)	0.7~1.1	Nm
Weight			26.5	g

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ELECTRICAL CHARACTERISTICS

$T_C=25^{\circ}\text{C}$ unless otherwise specified

Symbol	Parameter/Test Conditions		Min.	Typ.	Max.	Unit	
$V_{GE(th)}$	Gate Emitter Threshold Voltage	$V_{CE}=V_{GE}, I_C=4\text{mA}$	5.4	6.0	6.5	V	
$V_{CE(sat)}$	Collector Emitter Saturation Voltage	$I_C=100\text{A}, V_{GE}=15\text{V}, T_J=25^{\circ}\text{C}$		2.1	2.5		
		$I_C=100\text{A}, V_{GE}=15\text{V}, T_J=125^{\circ}\text{C}$		2.5			
I_{CES}	Collector Leakage Current	$V_{CE}=1200\text{V}, V_{GE}=0\text{V}, T_J=25^{\circ}\text{C}$			1	mA	
		$V_{CE}=1200\text{V}, V_{GE}=0\text{V}, T_J=125^{\circ}\text{C}$			10	mA	
I_{GES}	Gate Leakage Current	$V_{CE}=0\text{V}, V_{GE}=\pm 15\text{V}, T_J=25^{\circ}\text{C}$	-400		400	nA	
R_{gint}	Integrated Gate Resistor			7.5		Ω	
Q_g	Gate Charge	$V_{CE}=600\text{V}, I_C=100\text{A}, V_{GE}=15\text{V}$		0.47		μC	
C_{ies}	Input Capacitance	$V_{CE}=25\text{V}, V_{GE}=0\text{V}, f=1\text{MHz}$		6.2		nF	
C_{res}	Reverse Transfer Capacitance				0.35		nF
$t_{d(on)}$	Turn on Delay Time	$V_{CC}=600\text{V}, I_C=100\text{A}$ $R_G=7.5\Omega,$ $V_{GE}=\pm 15\text{V},$ Inductive Load	$T_J=25^{\circ}\text{C}$		150		ns
			$T_J=125^{\circ}\text{C}$		160		ns
t_r	Rise Time		$T_J=25^{\circ}\text{C}$		65		ns
			$T_J=125^{\circ}\text{C}$		70		ns
$t_{d(off)}$	Turn off Delay Time	$V_{CC}=600\text{V}, I_C=100\text{A}$ $R_G=7.5\Omega,$ $V_{GE}=\pm 15\text{V},$ Inductive Load	$T_J=25^{\circ}\text{C}$		400		ns
			$T_J=125^{\circ}\text{C}$		450		ns
t_f	Fall Time		$T_J=25^{\circ}\text{C}$		40		ns
			$T_J=125^{\circ}\text{C}$		60		ns
E_{on}	Turn on Energy	$V_{CC}=600\text{V}, I_C=100\text{A}$ $R_G=7.5\Omega,$ $V_{GE}=\pm 15\text{V},$ Inductive Load	$T_J=125^{\circ}\text{C}$		11.5		mJ
			$T_J=150^{\circ}\text{C}$		12.5		mJ
E_{off}	Turn off Energy		$T_J=125^{\circ}\text{C}$		5.5		mJ
			$T_J=150^{\circ}\text{C}$		6.0		mJ
I_{sc}	Short Circuit Current	$tp_{sc}\leq 10\mu\text{s}, V_{GE}=15\text{V}$ $T_J=125^{\circ}\text{C}, V_{CC}=600\text{V}$		400		A	
R_{thJC}	Junction to Case Thermal Resistance (Per IGBT)				0.27	K/W	

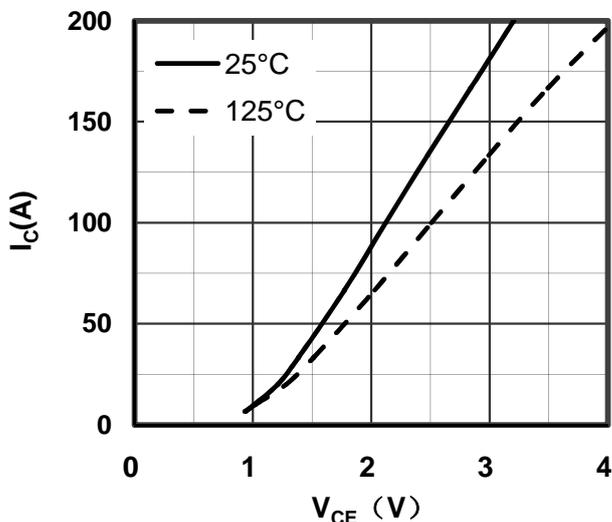


Figure 1. Typical Output Characteristics IGBT

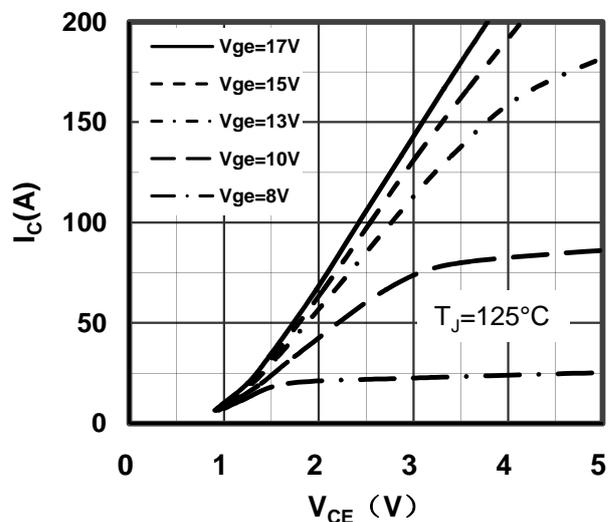


Figure 2. Typical Output Characteristics IGBT

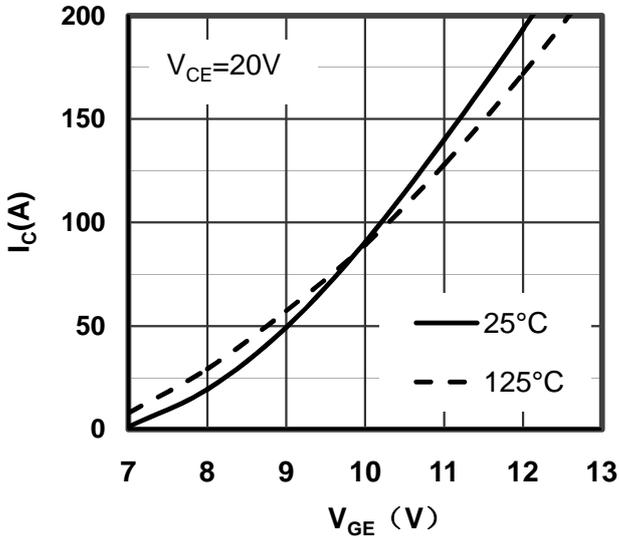


Figure 3. Typical Transfer characteristics IGBT

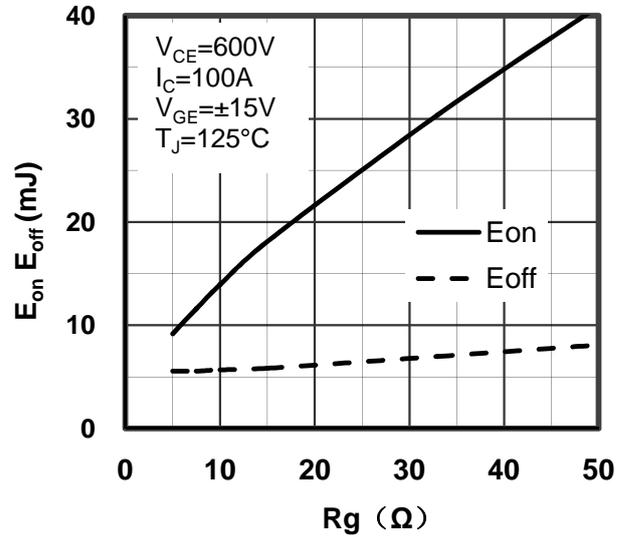


Figure 4. Switching Energy vs Gate Resistor IGBT

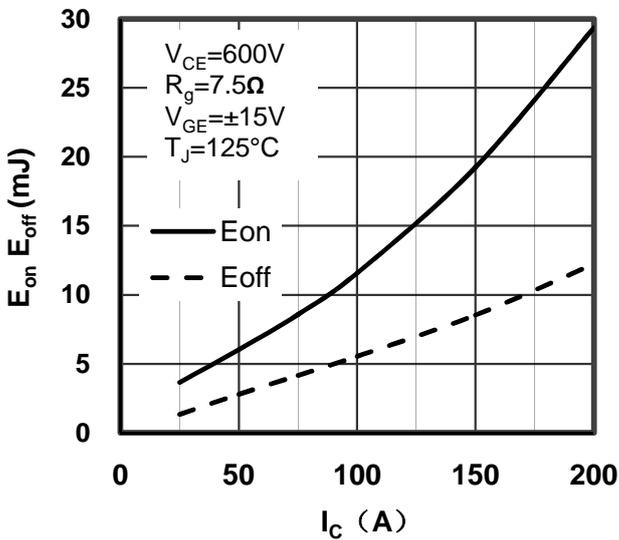


Figure 5. Switching Energy vs Collector Current IGBT

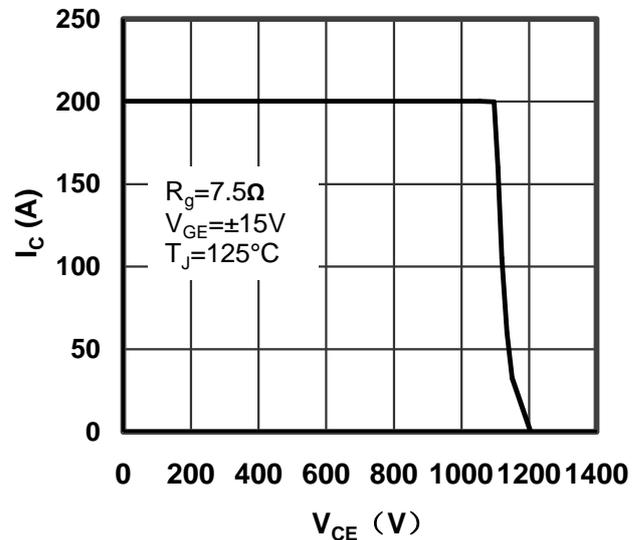


Figure 6. Reverse Biased Safe Operating Area IGBT

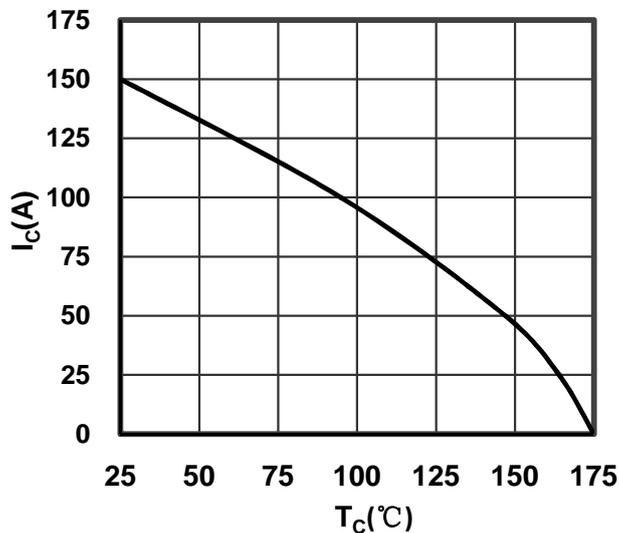


Figure 7. Collector Current vs Case temperature

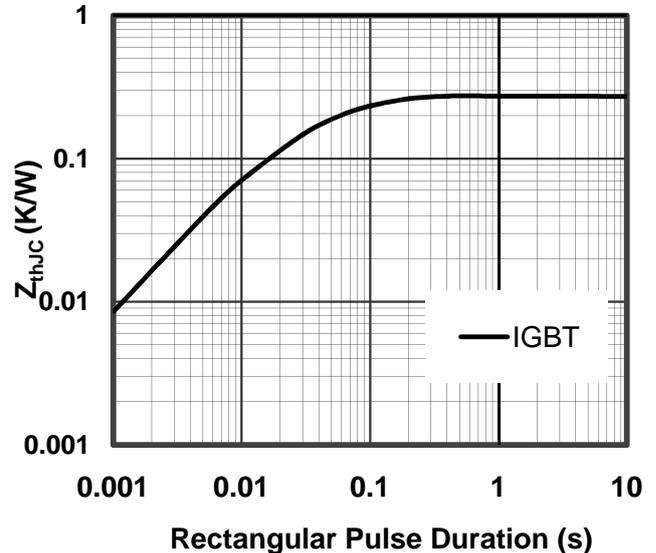
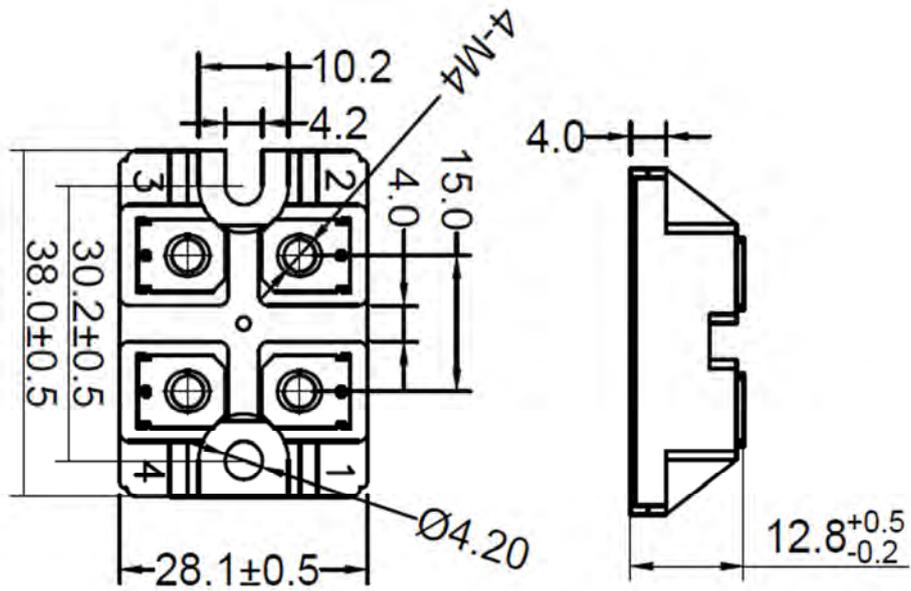


Figure 8. Transient Thermal Impedance of IGBT



Dimensions in (mm)
Figure 9. Package Outline